Electronic Supplementary Information (ESI)

High performance $La_2NiO_{4+\delta}$ oxygen and Ni-Ce_{0.9}Gd_{0.1}O_{2- δ} fuel electrodes for thin film reversible solid oxide cells

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Figure S1: Normalized conductance of a 1200 nm thick L2NO4 film grown on a YSZ substrate, measured at 300 $^{\circ}$ C using ECR, in response to a pO₂ variation from 10 to 250 mbar

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Figure S2: SEM micrographs of the pristine $NiCGO_{200mT-500C-TT}$ thin film (a) and after the annealing process (b).



Figure S3: SEM images of surfaces of the rSOC on the: (a) 1000 nm L2NO4 oxygen electrode side, and (b) 120 nm Ni-CGO fuel electrode side



Figure S4: Distribution of relaxation times (DRT) analysis of the rSOC EIS at OCV (1.1 V), in SOFC (0.7 V), and SOEC (1.3 V) operating modes at different temperatures: (a) 600 °C, (b) 550 °C, and (c) 500 °C